Reg. No.:					

Question Paper Code: 42407

B.E. / B.Tech. DEGREE EXAMINATION, NOV 2019

Second Semester

Electronics and Communication Engineering

14UEC207 - ELECTRONIC DEVICES

(Regulation 2014)

	Duration: Three hou	ırs		N	Maximum: 100 Marks		
		Ans	wer ALL Questi	ions			
		PART A	$A - (10 \times 1 = 10)$	Marks)			
1. Define Electron Volt.							
	(a) 2eV	(b) 1eV	(c) 9eV	(d) 7eV			
2. The energy gap decreases with the in temperature							
	(a) Constant	(b) unity	(c) decreases	(d) increas	ses		
3. Mention any one application of Zener Diode.							
	(a) detector			(b) tunnel diode			
	(c) For Control	ling the output	amplitude (d) d	lemodulation circ	uit		
4.	For every $10^{\circ}C$ rise	in temperature	the reverse satu	ration current app	proximately		
	(a) doubles	(b) halves	(c) re	emains the same	(d) decreases		
5.	By providing prope	r bias voltage ,t	the transistor car	n be made to worl	k as an		
	(a) amplifier	(b) regula	tor (c) swite	ch (d) di	ode		

6.	Mention the application of CC configuration					
	(a) low frequency circuits (b) high frequency circuits	(b) high frequency circuits				
	(c) audio frequency circuits (d) Impedance maching	(d) Impedance maching				
7.	When a FET acts as a voltage variable resistor?					
	(a) $Vgs=1$ (b) $Vgs=0$ (c) $Vgs<0$ (d) $Vgs>0$					
8.	Which mode JFET can operate					
	(a) depletion (b) enhancement					
	(c) depletion and enhancement (d) normal mode					
9.	In a tunnel diode, the width of the depletion layer is of the order of					
	(a) 0.1 micron (b) 1.0 micron					
	(c) 0.1 Armstrong (d) 100 Armstrong					
10.	LCD are used for display of					
	(a) printer (b) numeric only					
	(c) alphanumeric character only (d) numeric and alphanumeric character					
	PART - B (5 x $2 = 10 \text{ Marks}$)					
11.	Draw energy band diagram of semiconductor.					
12.	What is Zener break down?					
13.	Why CE configuration is widely used in amplifier circuits? Give reason.					
14.	List any four advantages of FET over conventional transistors.					
15.	Draw the energy band diagrams to show the operation of tunnel diode.					
	PART - C (5 x $16 = 80 \text{ Marks}$)					
	16. (a) (i) Explain the classification of semiconductor.					
	(ii) Give the short notes on drift and diffusion current.	(6)				
	Or					

		(b)	(i) Derive expression of Drift and Diffusion current.	(12)
			(ii) Write short Notes on Mass action law.	(4)
17.	(a)	(i)	Explain the effect of temperature on PN junction diodes.	(8)
		(ii)) Derive the diode current equation.	(8)
			Or	
	(b)	(i)	With the help of a circuit diagram explain the working of a half-wave rect Also draw the necessary waveforms. Also obtain the expression for the r factor and efficiency of rectification.	
		(ii)) Show that rectification efficiency for a half wave rectifier is 40.6%.	(4)
18.	(a)		escribe the following configuration and its characteristics (i) Common nfiguration (ii) Common emitter configuration.	base (16)
			Or	
	(b)) Dr	raw the block diagram of switched mode power supply and explain each block	(16)
19.	(a)		ith the help of suitable diagrams explain the working of different t MOSFET.	ypes (16)
			Or	
	(b)	Ex	aplain the construction and operation of N-channel JFET.	(16)
20.	(a)		With neat sketch explain the principle of Uni Junction Transistor) Differentiate between photoconductive and photovoltaic cells.	(12) (4)
			Or	
	(b)Wr	rite short notes on :	
		(i) I	LCD	(8)
		(ii)	CCD	(8)